

最终数据手册
英飞凌 耐短路 750V EDT2 IGBT 与快速软恢复二极管封装

特性

- $V_{CE} = 750\text{ V}$
- $I_C = 200\text{ A}$
- 行业领先最高功率密度, $I_C = 200\text{ A}$
- 750V集电极-发射极阻断电压能力
- 适用于 $470\text{ V } V_{DC}$ 系统, 并增加了 $400\text{ V } V_{DC}$ 系统的过压裕量
- 极低 $V_{CEsat} = 1.3\text{ V (typ.)}$, $I_{Cnom} = 200\text{ A}$, 25°C
- 短路耐受时间 $t_{sc} = 5\text{ }\mu\text{s}$ ($V_{CE} = 470\text{ V}$ 、 $V_{GE} = 15\text{ V}$)
- 短路条件下的自限电流
- 正温度系数和非常紧密的参数分布, 易于并联
- 由于 $I_{nom} = 200\text{ A}$, 减少了需要并联的器件数量
- 优异的并联均流能力
- 平滑的开关特性, 低EMI特征
- 低栅极电荷 Q_G
- 简单的栅极驱动器设计
- 配备快速软恢复发射极控制二极管 (Emcon3)
- TO247PLUS 封装, 爬电距离高达 6.6 mm
- 高可靠性

潜在应用

- 电动汽车遮阳器
- DC母线放电开关
- 汽车辅助驱动

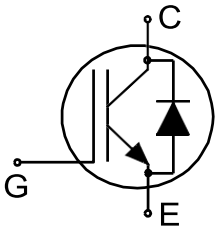
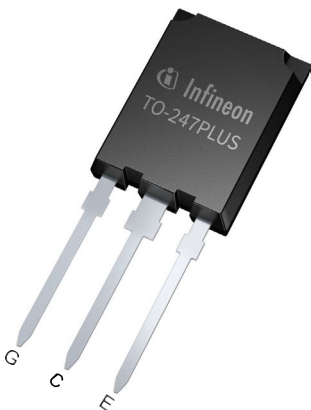
产品验证

- 车规级应用认证。
- 符合 AEC-Q101 标准

描述

封装引脚定义:

- 引脚 C & 背面 - 集电极
- 引脚 E - 发射极
- 引脚 G - 栅极



Type	Package	Marking
AIKQ200N75CP2	PG-TO247-3-U01	AKQ20FCP

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1 Package

表 1 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	Wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$			0.1	0.14	K/W
Diode thermal resistance, junction-case	$R_{th(j-c)}$			0.2	0.26	K/W

2 IGBT

表 2 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}			750	V
DC collector current, limited by T_{vjmax}	I_C		$T_c = 25\text{ °C}$	200	A
			$T_c = 100\text{ °C}$	200	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}			600	A
Turn-off safe operating area		$V_{CE} \leq 750\text{ V}$, $t_p = 1\text{ }\mu\text{s}$, $T_{vj} \leq 175\text{ °C}$		600	A
Gate-emitter voltage	V_{GE}			± 20	V
Transient gate-emitter voltage	V_{GE}	$t_p < 0.1\text{ }\mu\text{s}$, $D < 0.01$		± 30	V
Short-circuit withstand time	t_{SC}	$V_{CC} \leq 470\text{ V}$, $V_{GE} = 15\text{ V}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}$, $T_{vj} = 25\text{ °C}$		5	μs
Power dissipation	P_{tot}		$T_c = 25\text{ °C}$	1071	W
			$T_c = 100\text{ °C}$	535	

表3 **特征值**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = 200\text{ A}$, $V_{GE} = 15\text{ V}$	$T_{vj} = 25\text{ °C}$	1.2	1.3	1.5	V
			$T_{vj} = 175\text{ °C}$		1.6		
Gate-emitter threshold voltage	V_{GEth}	$I_C = 2.6\text{ mA}$, $V_{CE} = V_{GE}$		5.2	5.8	6.4	V
Zero gate-voltage collector current	I_{CES}	$V_{CE} = 750\text{ V}$, $V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$			200	μA
			$T_{vj} = 175\text{ °C}$		6000		
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$				100	nA
Transconductance	g_{fs}	$I_C = 200\text{ A}$, $V_{CE} = 20\text{ V}$			140		S
Short-circuit collector current	I_{SC}	$V_{CC} \leq 470\text{ V}$, $V_{GE} = 15\text{ V}$, $t_{SC} \leq 5\text{ }\mu\text{s}$, Allowed number of short circuits < 1000, Time between short circuits $\geq 1.0\text{ s}$, $T_{vj} = 25\text{ °C}$	$T_{vj} = 25\text{ °C}$		1250		A
Input capacitance	C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 100\text{ kHz}$			21300		pF
Output capacitance	C_{oes}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 100\text{ kHz}$			535		pF
Reverse transfer capacitance	C_{res}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 100\text{ kHz}$			93		pF
Gate charge	Q_G	$V_{CC} = 600\text{ V}$, $I_C = 200\text{ A}$			1260		nC
Turn-on delay time	$t_{d(on)}$	$V_{GE} = -8/15\text{ V}$, $R_{G(on)} = 5\text{ }\Omega$, $R_{G(off)} = 5\text{ }\Omega$, $L_\sigma = 50\text{ nH}$, $C_\sigma = 30\text{ pF}$	$T_{vj} = 25\text{ °C}$, $I_C = 200\text{ A}$		89		ns
			$T_{vj} = 175\text{ °C}$, $I_C = 200\text{ A}$		85		
Rise time (inductive load)	t_r	$V_{GE} = -8/15\text{ V}$, $R_{G(on)} = 5\text{ }\Omega$, $R_{G(off)} = 5\text{ }\Omega$, $L_\sigma = 50\text{ nH}$, $C_\sigma = 30\text{ pF}$	$T_{vj} = 25\text{ °C}$, $I_C = 200\text{ A}$		120		ns
			$T_{vj} = 175\text{ °C}$, $I_C = 200\text{ A}$		117		
Turn-off delay time	$t_{d(off)}$	$V_{GE} = -8/15\text{ V}$, $R_{G(on)} = 5\text{ }\Omega$, $R_{G(off)} = 5\text{ }\Omega$, $L_\sigma = 50\text{ nH}$, $C_\sigma = 30\text{ pF}$	$T_{vj} = 25\text{ °C}$, $I_C = 200\text{ A}$		266		ns
			$T_{vj} = 175\text{ °C}$, $I_C = 200\text{ A}$		284		
Fall time (inductive load)	t_f	$V_{GE} = -8/15\text{ V}$, $R_{G(on)} = 5\text{ }\Omega$, $R_{G(off)} = 5\text{ }\Omega$, $L_\sigma = 50\text{ nH}$, $C_\sigma = 30\text{ pF}$	$T_{vj} = 25\text{ °C}$, $I_C = 200\text{ A}$		46		ns
			$T_{vj} = 175\text{ °C}$, $I_C = 200\text{ A}$		60		

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表 3 (续) 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-on energy ¹⁾	E_{on}	$V_{GE} = -8/15\text{ V}$, $R_{G(on)} = 5\ \Omega$, $R_{G(off)} = 5\ \Omega$, $L_{\sigma} = 50\text{ nH}$, $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$, $I_c = 200\text{ A}$		15.3		mJ
			$T_{vj} = 175\text{ }^{\circ}\text{C}$, $I_c = 200\text{ A}$		16.3		
Turn-off energy	E_{off}	$V_{GE} = -8/15\text{ V}$, $R_{G(on)} = 5\ \Omega$, $R_{G(off)} = 5\ \Omega$, $L_{\sigma} = 50\text{ nH}$, $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$, $I_c = 200\text{ A}$		7		mJ
			$T_{vj} = 175\text{ }^{\circ}\text{C}$, $I_c = 200\text{ A}$		8.1		
Total switching energy	E_{ts}	$V_{GE} = -8/15\text{ V}$, $R_{G(on)} = 5\ \Omega$, $R_{G(off)} = 5\ \Omega$, $L_{\sigma} = 50\text{ nH}$, $C_{\sigma} = 30\text{ pF}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$, $I_c = 200\text{ A}$		22.3		mJ
			$T_{vj} = 175\text{ }^{\circ}\text{C}$, $I_c = 200\text{ A}$		24.4		
Operating junction temperature	T_{vj}			-40		175	$^{\circ}\text{C}$

1)包括反向恢复损耗

3 二极管

表4 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Diode forward current, limited by T_{vjmax}	I_F		$T_c = 25\text{ }^{\circ}\text{C}$	200	A
			$T_c = 100\text{ }^{\circ}\text{C}$	200	
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpulse}			600	A
Power dissipation	P_{tot}		$T_c = 25\text{ }^{\circ}\text{C}$	576	W
			$T_c = 100\text{ }^{\circ}\text{C}$	288	

表5 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	$I_F = 200\text{ A}$	$T_{vj} = 25\text{ }^{\circ}\text{C}$		1.8	1.95	V
			$T_{vj} = 175\text{ }^{\circ}\text{C}$		1.9		

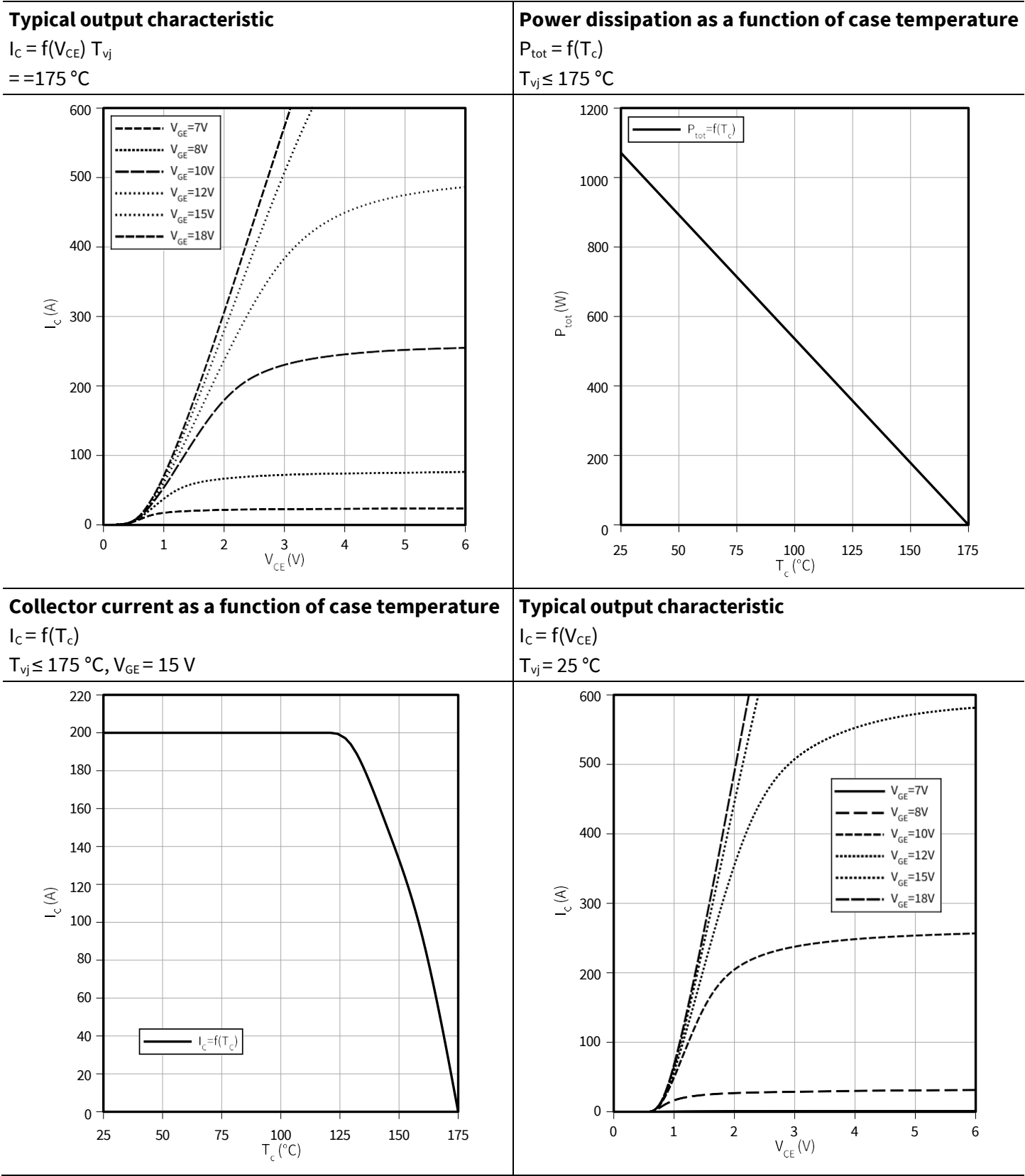
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表 5 (续) 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode reverse recovery charge	Q_{rr}	$V_R < 470 \text{ V}, R_{G(on)} = 4.8 \Omega$	$T_{vj} = 25 \text{ }^{\circ}\text{C},$ $I_F = 200 \text{ A},$ $-di_F/dt = 1060 \text{ A}/\mu\text{s}$		4.7		μC
			$T_{vj} = 175 \text{ }^{\circ}\text{C},$ $I_F = 200 \text{ A},$ $-di_F/dt = 1110 \text{ A}/\mu\text{s}$		7.5		
Diode peak reverse recovery current	I_{rrm}	$V_R < 470 \text{ V}, R_{G(on)} = 4.8 \Omega$	$T_{vj} = 25 \text{ }^{\circ}\text{C},$ $I_F = 200 \text{ A},$ $-di_F/dt = 1060 \text{ A}/\mu\text{s}$		41		A
			$T_{vj} = 175 \text{ }^{\circ}\text{C},$ $I_F = 200 \text{ A},$ $-di_F/dt = 1110 \text{ A}/\mu\text{s}$		56		
Reverse recovery energy	E_{rec}	$V_R < 470 \text{ V}, V_{GE} = -8/15 \text{ V},$ $R_{G(on)} = 4.8 \Omega, L_{\sigma} = 50 \text{ nH},$ $C_{\sigma} = 30 \text{ pF}$	$T_{vj} = 25 \text{ }^{\circ}\text{C},$ $-di_F/dt = 1060 \text{ A}/\mu\text{s}$		1.32		mJ
			$T_{vj} = 175 \text{ }^{\circ}\text{C},$ $-di_F/dt = 1110 \text{ A}/\mu\text{s}$		2.16		
Operating junction temperature	T_{vj}			-40		175	$^{\circ}\text{C}$

4 特性图

4 特性图

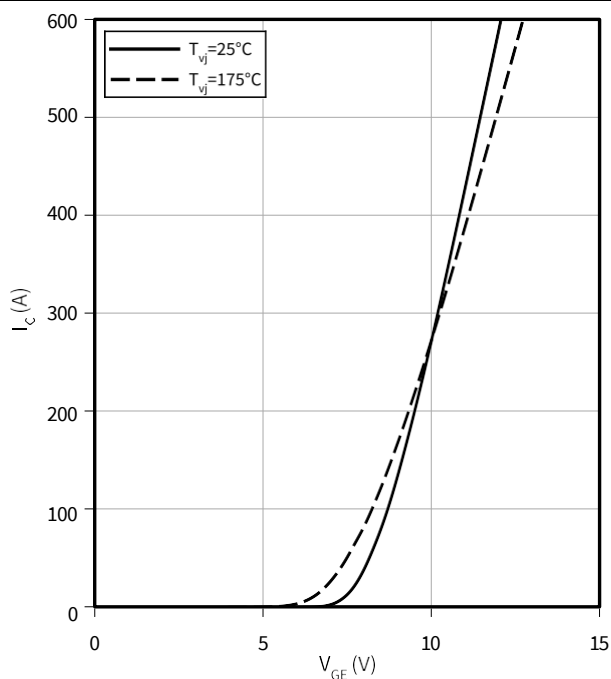


4 特性图

Typical transfer characteristic

$$I_C = f(V_{GE})$$

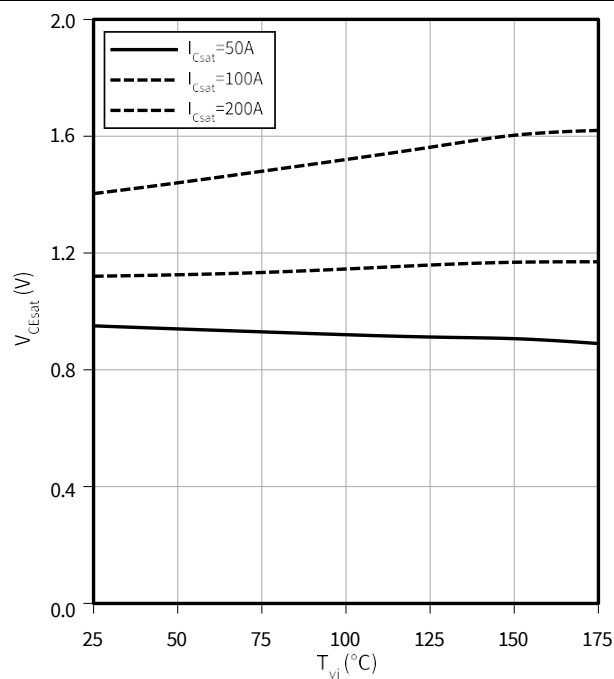
$$V_{CE} = 20 \text{ V}$$



Typical collector-emitter saturation voltage as a function of junction temperature

$$V_{CEsat} = f(T_{vj})$$

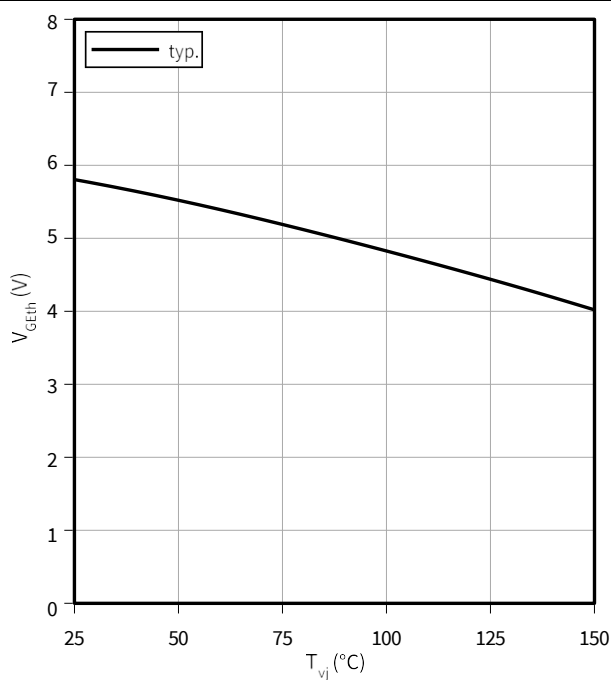
$$V_{GE} = 15 \text{ V}$$



Typical Gate-emitter threshold voltage as a function of junction temperature

$$V_{GEth} = f(T_{vj})$$

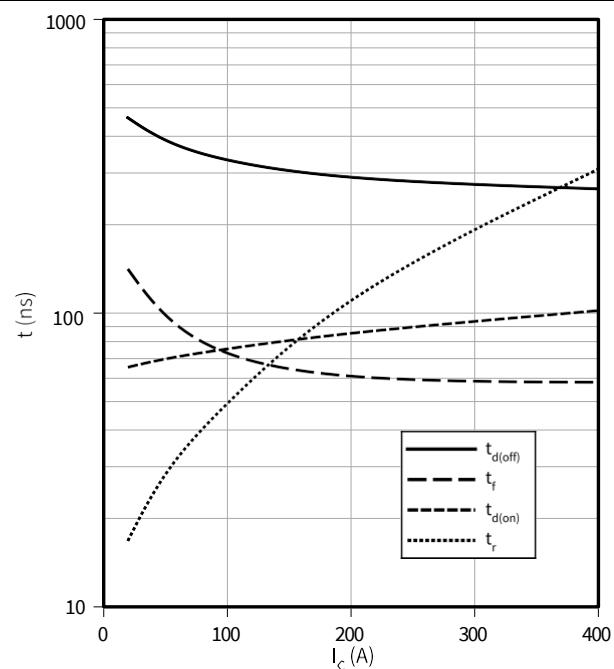
$$I_C = 2.60 \text{ mA}$$



Typical switching times as a function of collector current

$$t = f(I_C)$$

$$R_{G(off)} = 5 \Omega, V_{CE} = 470 \text{ V}, T_{vj} = 175^\circ\text{C}, V_{GE} = -8/15 \text{ V}, R_{G(on)} = 5 \Omega$$

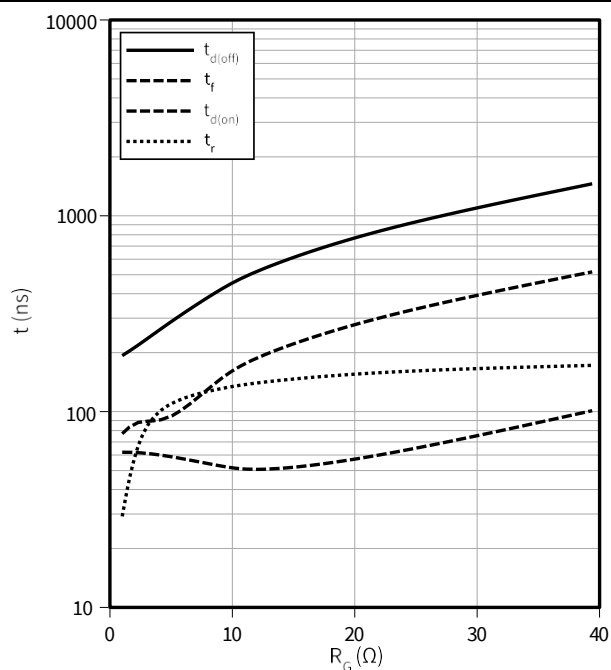


4 特性图

Typical switching times as a function of gate resistor

$t = f(R_G)$

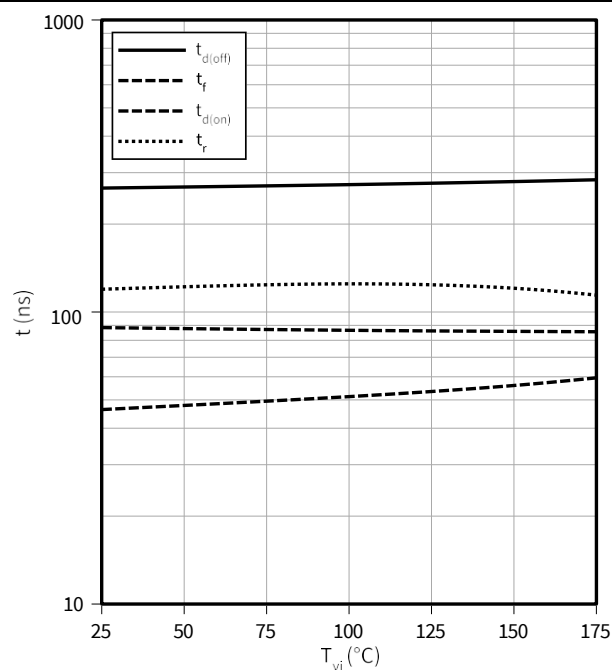
$I_C = 200 \text{ A}$, $V_{CE} = 470 \text{ V}$, $T_{vj} = 175 \text{ }^\circ\text{C}$, $V_{GE} = -8/15 \text{ V}$



Typical switching times as a function of junction temperature

$t = f(T_{vj})$

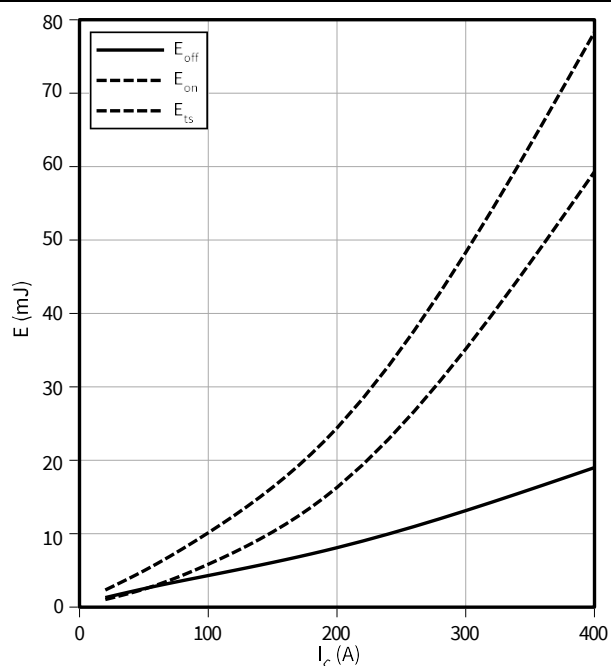
$I_C = 200 \text{ A}$, $R_{G(off)} = 5.0 \text{ } \Omega$, $V_{CE} = 470 \text{ V}$, $V_{GE} = -8/15 \text{ V}$, $R_{G(on)} = 5 \text{ } \Omega$



Typical switching energy losses as a function of collector current

$E = f(I_C)$

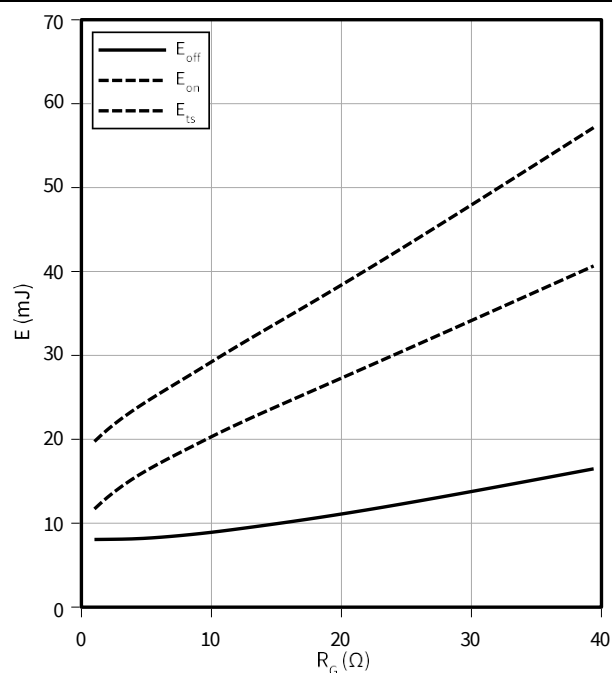
$R_{G(off)} = 5 \text{ } \Omega$, $V_{CE} = 470 \text{ V}$, $T_{vj} = 175 \text{ }^\circ\text{C}$, $V_{GE} = -8/15 \text{ V}$, $R_{G(on)} = 5 \text{ } \Omega$



Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

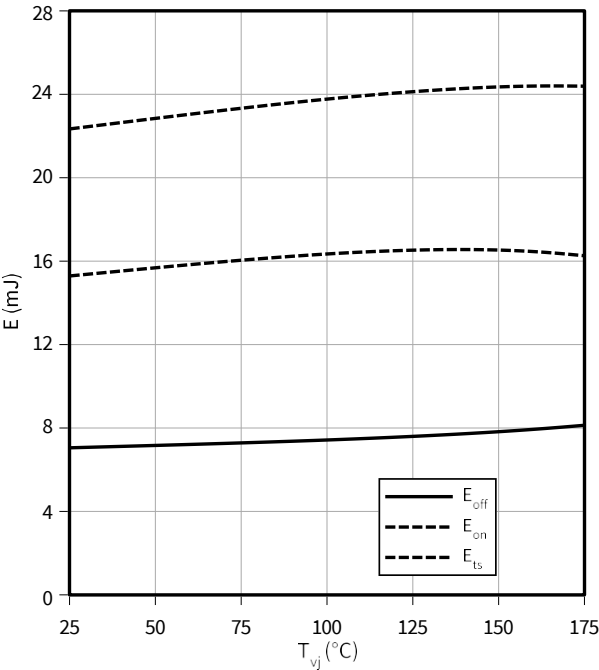
$I_C = 200 \text{ A}$, $V_{CE} = 470 \text{ V}$, $T_{vj} = 175 \text{ }^\circ\text{C}$, $V_{GE} = -8/15 \text{ V}$



4 特性图

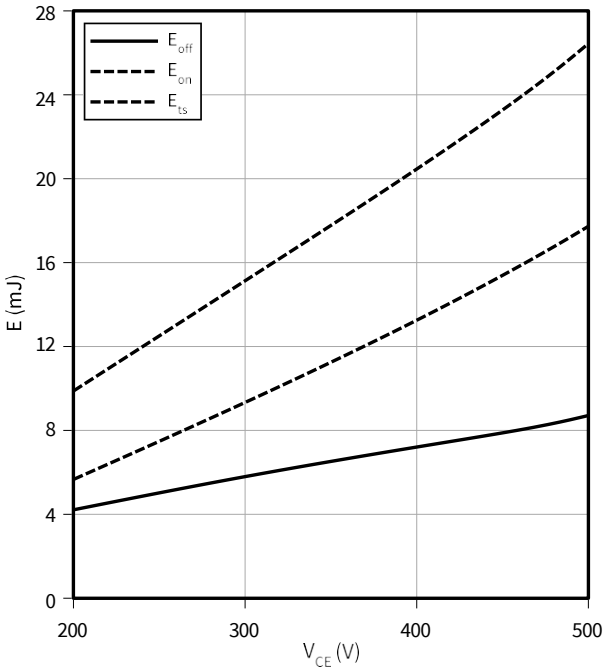
Typical switching energy losses as a function of junction temperature

$E = f(T_{vj})$
 $I_C = 200\text{ A}$, $R_{G(off)} = 5.0\ \Omega$, $V_{CE} = 470\text{ V}$, $V_{GE} = -8/15\text{ V}$, $R_{G(on)} = 5\ \Omega$



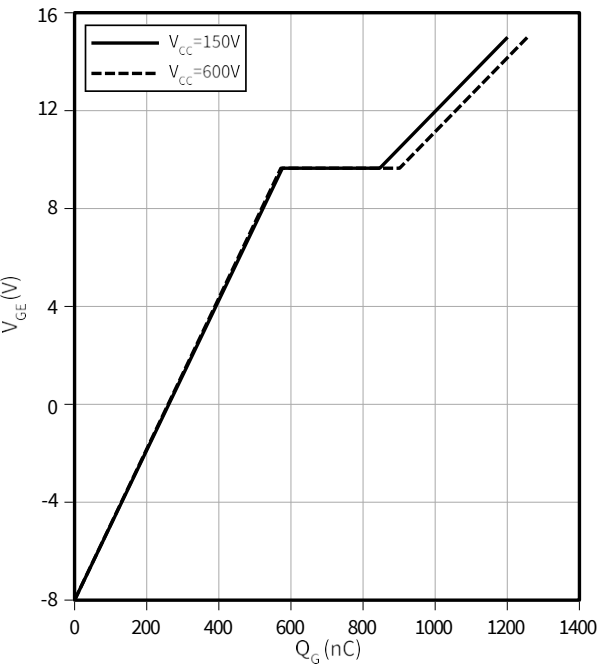
Typical switching energy losses as a function of collector emitter voltage

$E = f(V_{CE})$
 $I_C = 200\text{ A}$, $R_{G(off)} = 5\ \Omega$, $T_{vj} \leq 175\text{ °C}$, $V_{GE} = -8/15\text{ V}$, $R_{G(on)} = 5\ \Omega$



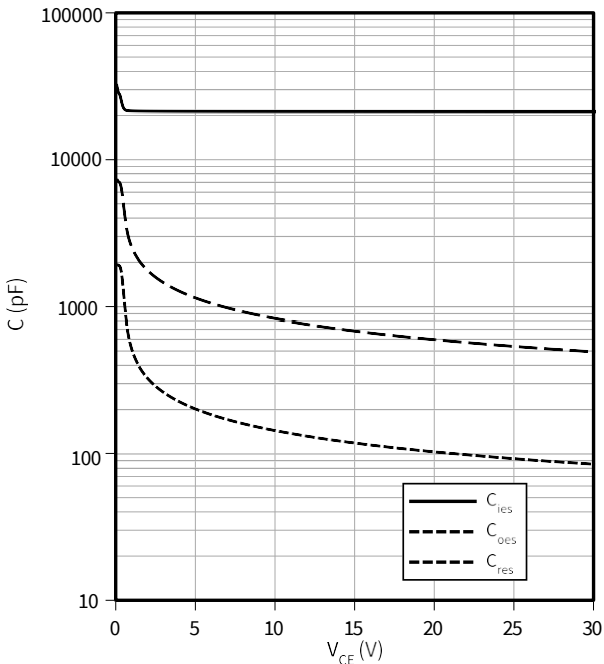
Typical gate charge

$V_{GE} = f(Q_G)$
 $I_C = 200\text{ A}$



Typical capacitance as a function of collector-emitter voltage

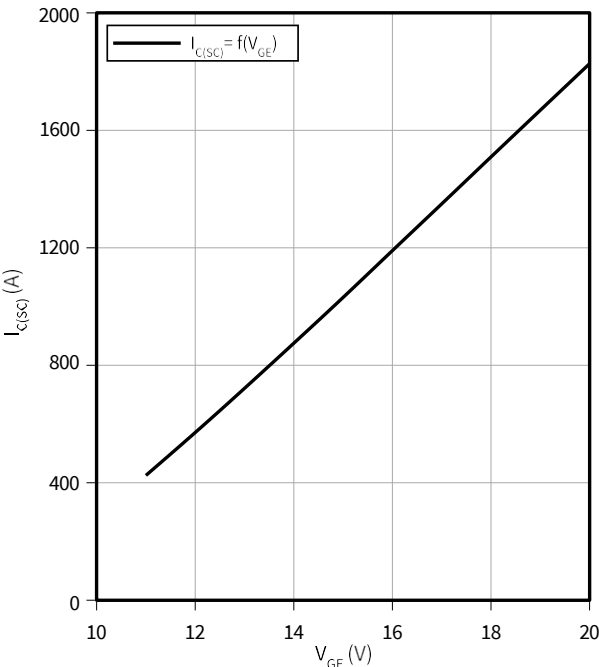
$C = f(V_{CE})$
 $f = 100\text{ kHz}$, $V_{GE} = 0\text{ V}$



4 特性图

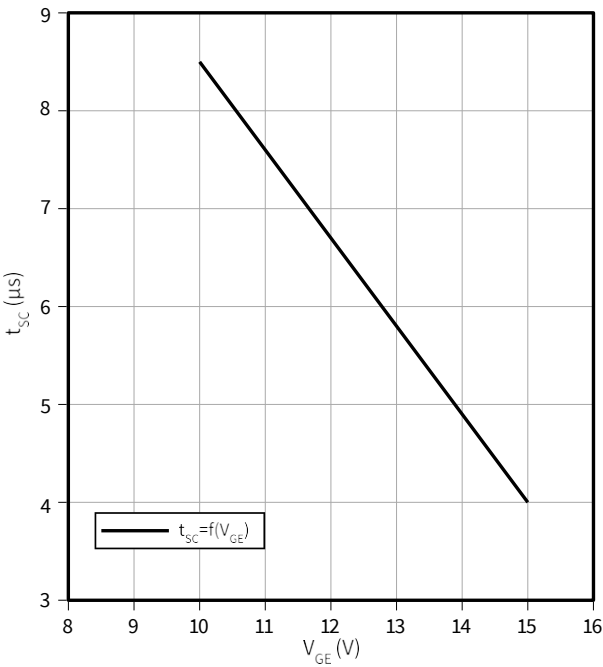
Typical short circuit collector current as a function of gate-emitter voltage

$I_{C(SC)} = f(V_{GE})$
 $T_{vj} \leq 175\text{ }^{\circ}\text{C}, V_{CC} \leq 470\text{ V}$



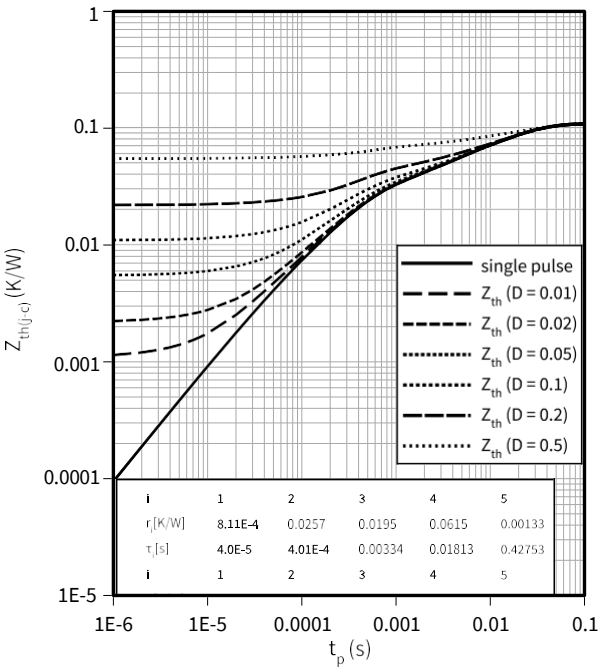
Typical Short circuit withstand time as a function of gate-emitter voltage

$t_{SC} = f(V_{GE})$
 $T_{vj} \leq 175\text{ }^{\circ}\text{C}, V_{CC} \leq 470\text{ V}$



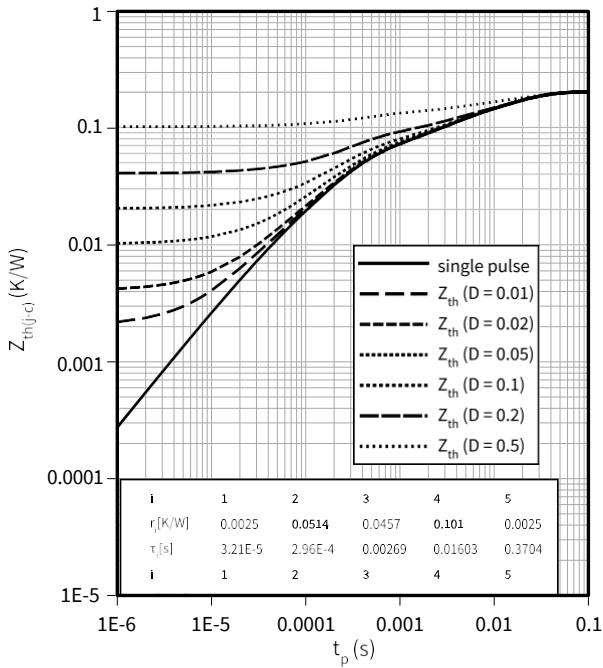
IGBT typical transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$
 $D = t_p/T$



Diode typical transient thermal impedance as a function of pulse width

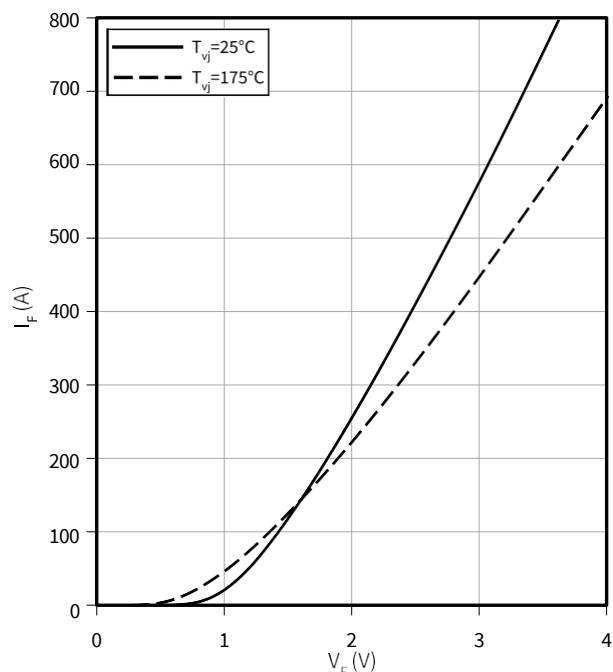
$Z_{th(j-c)} = f(t_p)$
 $D = t_p/T$



4 特性图

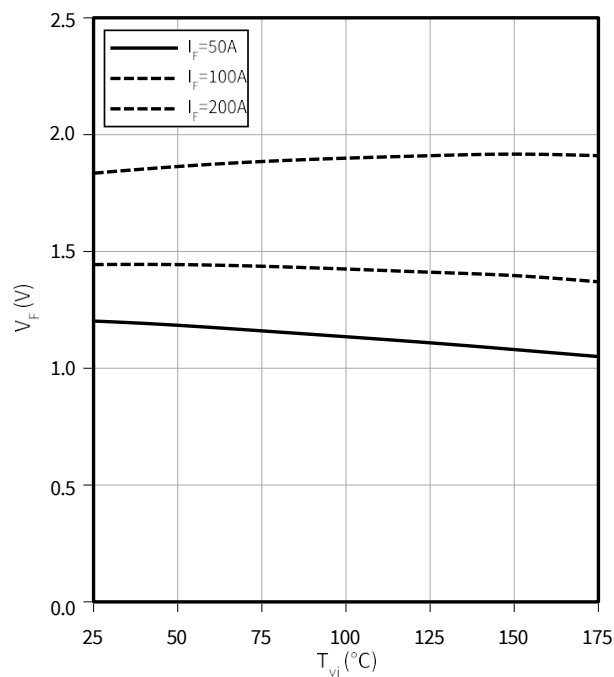
Typical diode forward current as a function of forward voltage

$$I_F = f(V_F)$$



Typical diode forward voltage as a function of junction temperature

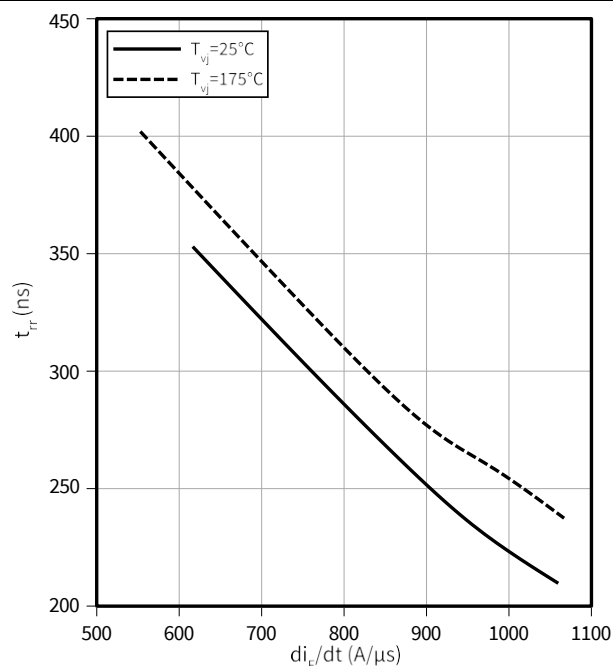
$$V_F = f(T_{vj})$$



Typical reverse recovery time as a function of diode current slope

$$t_{rr} = f(di_F/dt)$$

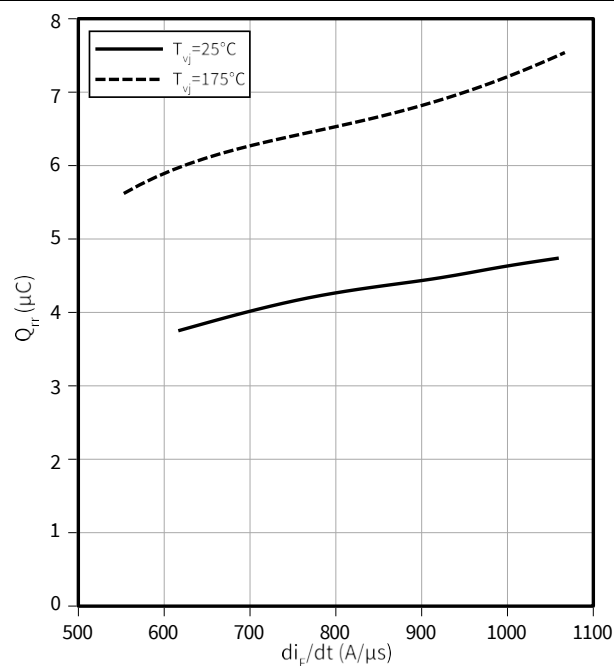
$$V_R < 470\text{ V}, I_F = 200\text{ A}$$



Typical reverse recovery charge as a function of diode current slope

$$Q_{rr} = f(di_F/dt)$$

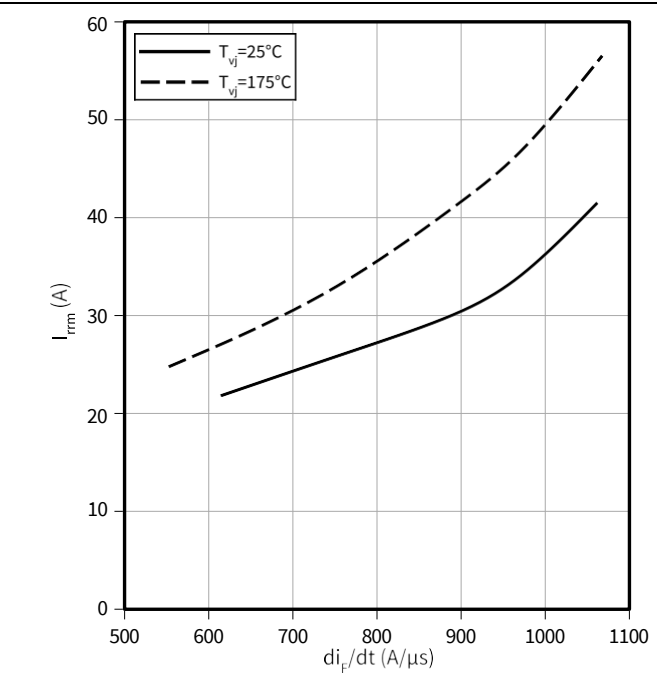
$$V_R < 470\text{ V}, I_F = 200\text{ A}$$



4 特性图

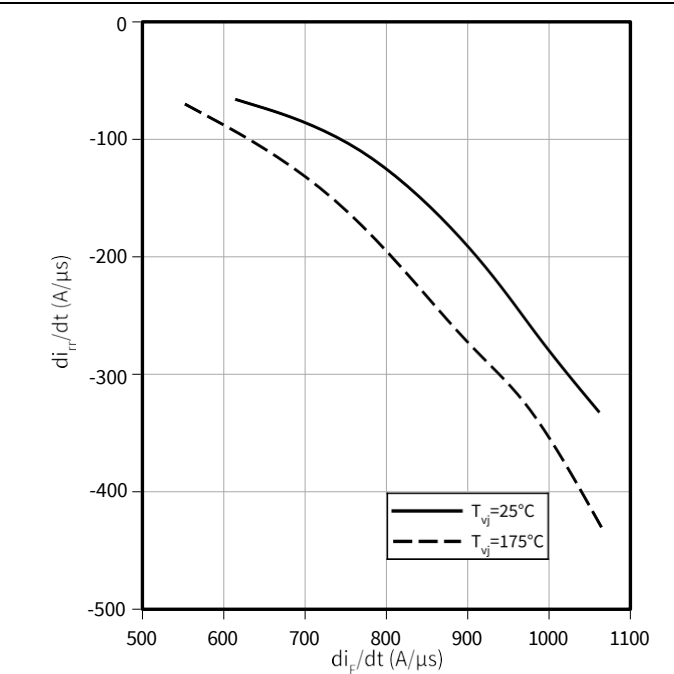
Typical reverse recovery current as a function of diode current slope

$I_{rrm} = f(di_F/dt)$
 $V_R < 470\text{ V}, I_F = 200\text{ A}$



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

$di_{rr}/dt = f(di_F/dt)$
 $V_R < 470\text{ V}, I_F = 200\text{ A}$



5 封装外形

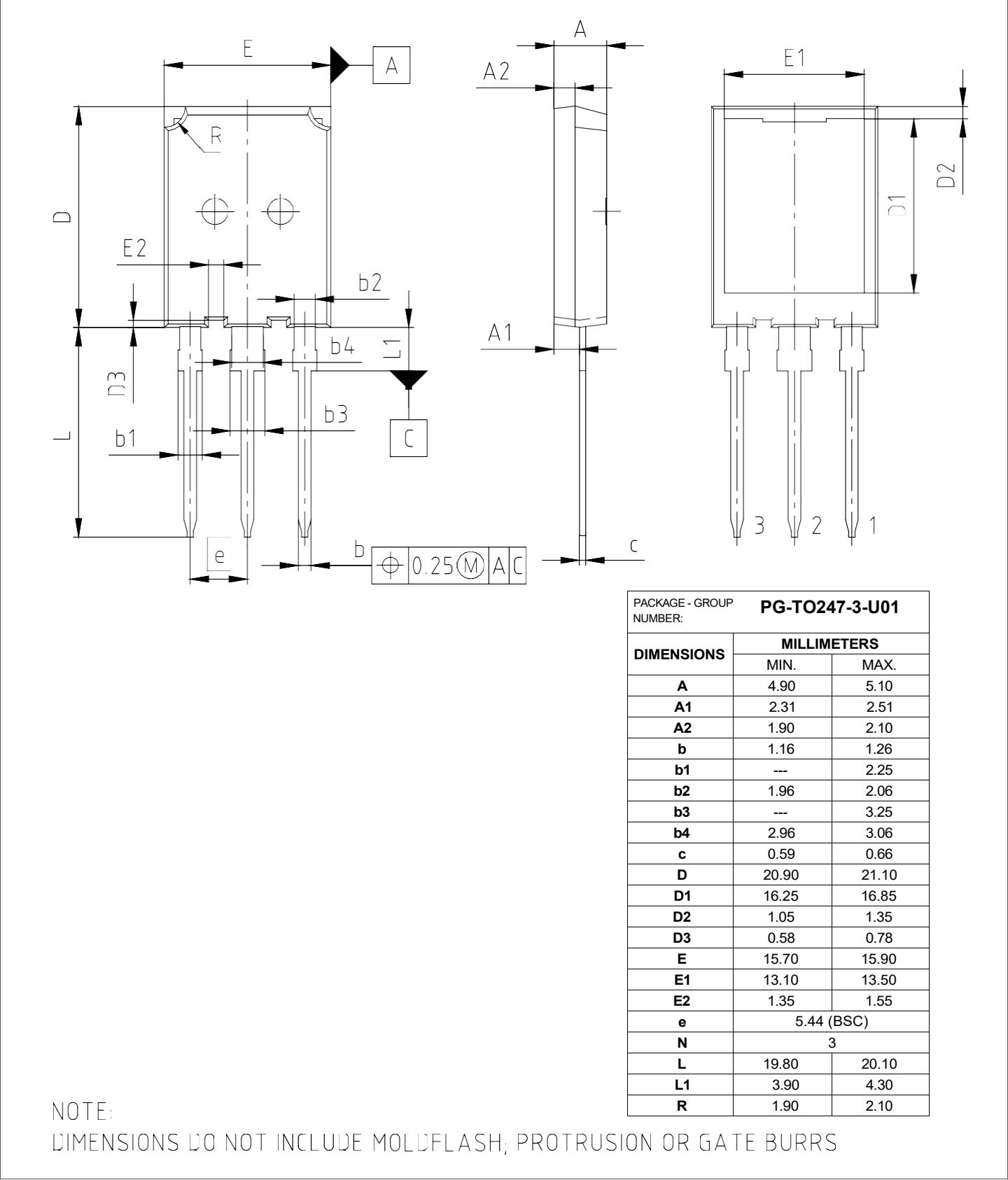


图 1

修订记录

修订记录

Document revision	Date of release	Description of changes
V0.1	2020-07-16	Target
V0.1	2020-10-09	Target
V0.2	2020-11-02	Updated marking on page1
n/a	2020-11-30	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.00	2022-02-16	Final datasheet
1.10	2022-03-28	Updated Isc and Rthjc
1.20	2025-06-11	Package drawing, transient thermal impedance plots, and qualification labels updated according to the latest guidelines
1.30	2025-07-03	Qualification labels updated according to the latest guidelines



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